High Speed Silicon Photodiodes

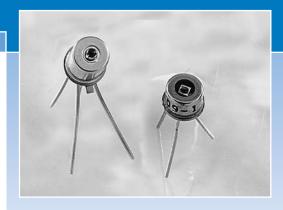
High Speed Silicon Series

Typical Capacitance vs. Reverse Bias

OSI Optoelectronics High Speed Silicon series are small area devices optimized for fast response time or High bandwith applications. The BPX-65 complements the rest of the high speed group with an industry standard.

The spectral range for these devices goes from 350 nm to 1100 nm. The responsivity and response time are optimized such that the HR series exhibit a peak responsivity of 0.50 A/W at 800 nm and typical response times of a few hundred pico seconds at -5V.

Note that for all high-speed photodetectors, a reverse bias is required to achieve the fastest response times. However, the reverse bias should be limited to maximum reverse voltage specified to avoid damage to the detector. Output signals can be measured directly with an oscilloscope or coupled to high frequency amplifiers as shown in figure 10 of the Photodiode Characteristics section of the catalog. All parts in the High-Speed silicon series are available with a flat window or ball lens (L).

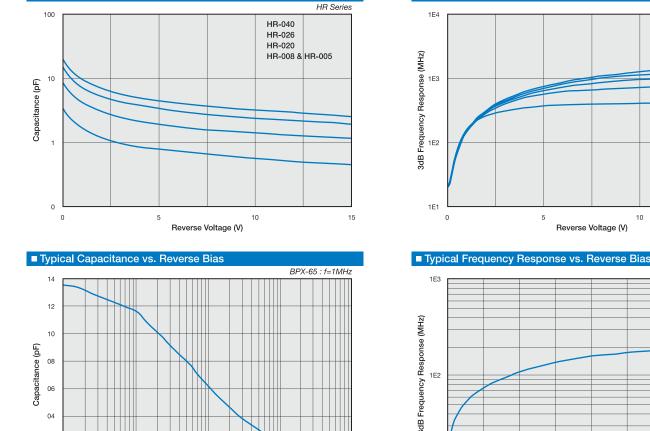


APPLICATIONS

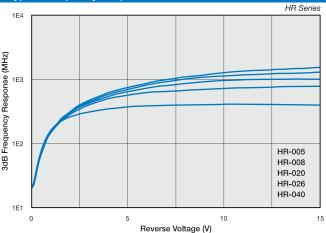
- Video Systems
- Computers and Peripherals
- Industrial Control
- Guidance Systems
- Laser Monitoring

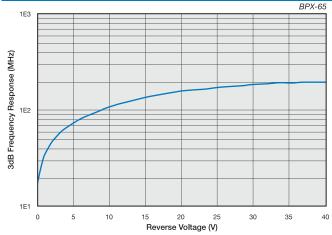
FEATURES

- Low Dark Current
- Low Capacitance
- TO-46 Package
- w/Lensed Cap
- Sub ns Response



Typical Frequency Response vs. Reverse Bias





100

10

02 0

0.01

0.1

Reverse Voltage (V)

Typical Electro-Optical Specifications at T_A=23°C

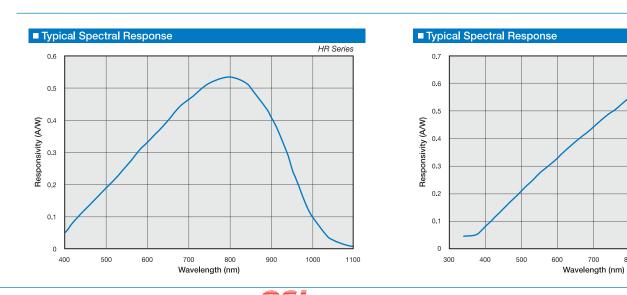
nber	Active Area		ength	Responsivity (A/W)		Capacitance	Dark Current		NEP (W/√Hz)	Reverse Voltage	Rise Time § (ns) ‡	Tem Ran (°	nge	
Model Number	Area (mm²)	Dimensions (mm) Peak Wavel	Peak Wavelength (nm)	830 nm		(pF) ‡	(nA) ‡		830 nm	(V)	830 nm 50 Ω	Operating	Storage	Package Style ¶
Σ	Area	Dime (rr	Pe	min.	typ.	typ.	typ.	max.	typ.	max.	typ.	Oper	Sto	
High Responsivity Series (V _{BIAS} =-5 V)														
PIN-HR005 PIN-HR005L*	0.01	0.127φ	800	0.45*	0.50*	0.8	0.03	0.8	5.0 e-15	15	0.60	-25 ~ +85	-40 ~ +100	9 / TO-18 16 / TO-18 (L - Ball Lens Cap)
PIN-HR008 PIN-HR008L*	0.04	0.203 sq				0.8	0.03	0.8	5.0 e-15		0.60			
PIN-HR020 PIN-HR020L*	0.20	0.508 ¢				1.8	0.06	1.0	7.1 e-15		0.80			
PIN-HR026 PIN-HR026L*	0.34	0.660 ø				2.6	0.1	1.5	1.0 e-14		0.90			
PIN-HR040 PIN-HR040L*	0.77	0.991 ¢				4.9	0.3	2.0	1.9 e-14		1.0		-4	
BPX-65 (V _{BIAS} =-20 V)														
BPX-65	1.0	1.0 sq	900	0.45	0.5	3.0	0.5	5.0	2.3 e-14	50	2.0			7 / TO-18
nber	Acti	ve Area 🛔		Responsivity (A/W)		Capacitance (pF) ‡	Dark Current (nA) ‡		NEP (W/√Hz)	Reverse Voltage (V)	Rise Time § (ns) ‡	Temp.** Range (°C)		
Model Number	Area (mm²)	Area (mm²) Dimensions (mm) Peak Wavelength (nm)		900 nm					900 nm		820 nm	Operating Storage	Storage	Package Style ¶
Σ	Area	Dime (n	Ре	min.	typ.	typ.	typ.	max.	typ.	max.	typ.	Ope	Sto	

BPX-65R (V_{BTAS} =-20 V)

BPX-65R	1.0	1.0 sq	850	0.52	0.55	3.5	1.0	5.0	3.3 e-14	30	3.5	-40 ~ +80	-55 ~ +100	4 / TO-18

¶ For mechanical drawing, please refer to pages 58 thru 69.
* Responsivities are measured for Flat window devices. L- Refers to devices with a Ball-type lens cap.

Chip centering is within +/- 0.005" wrt OD of the Header. ** Non-Condensing temperature and Storage Range, Non-Condensing Environment. Cathode on BPX-65R is connected to the case.



800

900

1000

1100

BPX-65

AVOID DIRECT LIGHT

Since the spectral response of silicon photodiode includes the visible light region, care must be taken to avoid photodiode exposure to high ambient light levels, particularly from tungsten sources or sunlight. During shipment from OSI Optoelectronics, your photodiodes are packaged in opaque, padded containers to avoid ambient light exposure and damage due to shock from dropping or jarring.

AVOID SHARP PHYSICAL SHOCK

Photodiodes can be rendered inoperable if dropped or sharply jarred. The wire bonds are delicate and can become separated from the photodiode's bonding pads when the detector is dropped or otherwise receives a sharp physical blow.

CLEAN WINDOWS WITH OPTICAL GRADE CLOTH / TISSUE

Most windows on OSI Optoelectronics photodiodes are either silicon or quartz. They should be cleaned with isopropyl alcohol and a soft (optical grade) pad.

OBSERVE STORAGE TEMPERATURES AND HUMIDITY LEVELS

Photodiode exposure to extreme high or low storage temperatures can affect the subsequent performance of a silicon photodiode. Storage temperature guidelines are presented in the photodiode performance specifications of this catalog. Please maintain a non-condensing environment for optimum performance and lifetime.

OBSERVE ELECTROSTATIC DISCHARGE (ESD) PRECAUTIONS

OSI Optoelectronics photodiodes, especially with IC devices (e.g. Photops) are considered ESD sensitive. The photodiodes are shipped in ESD protective packaging. When unpacking and using these products, anti-ESD precautions should be observed.

DO NOT EXPOSE PHOTODIODES TO HARSH CHEMICALS

Photodiode packages and/or operation may be impaired if exposed to CHLOROTHENE, THINNER, ACETONE, or TRICHLOROETHYLENE.

INSTALL WITH CARE

Most photodiodes in this catalog are provided with wire or pin leads for installation in circuit boards or sockets. Observe the soldering temperatures and conditions specified below:

Soldering Iron:	Soldering 30 W or le Temperature at tip o	ess of iron 300°C or lower.
Dip Soldering:	Bath Temperature: Immersion Time: Soldering Time:	260±5°C. within 5 Sec. within 3 Sec.
Vapor Phase Soldering:	DO NOT USE	
Reflow Soldering:	DO NOT USE	

Photodiodes in plastic packages should be given special care. Clear plastic packages are more sensitive to environmental stress than those of black plastic. Storing devices in high humidity can present problems when soldering. Since the rapid heating during soldering stresses the wire bonds and can cause wire to bonding pad separation, it is recommended that devices in plastic packages to be baked for 24 hours at 85°C.

The leads on the photodiode **SHOULD NOT BE FORMED**. If your application requires lead spacing modification, please contact OSI Optoelectronics Applications group at (310)978-0516 before forming a product's leads. Product warranties could be voided.

1. Parameter Definitions:

- A = Distance from top of chip to top of glass.
- a = Photodiode Anode.
- B = Distance from top of glass to bottom of case.
- c = Photodiode Cathode
 - (Note: cathode is common to case in metal package products unless otherwise noted).
- W = Window Diameter.
- F.O.V. = Filed of View (see definition below).

2. Dimensions are in inches (1 inch = 25.4 mm).

3. Pin diameters are 0.018 ± 0.002" unless otherwise specified.

4. Tolerances (unless otherwise noted) General: 0.XX ±0.01" 0.XXX ±0.005" Chip Centering: ±0.010"

Dimension 'A': ±0.015"

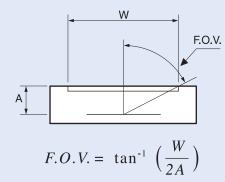
5. Windows

All '**UV**' Enhanced products are provided with QUARTZ glass windows, 0.027 \pm 0.002" thick.

All 'XUV' products are provided with removable windows.

All '**DLS**' PSD products are provided with A/R coated glass windows.

All 'FIL' photoconductive and photovoltaic products are epoxy filled instead of glass windows.





Mechanical Specifications and Die Topography

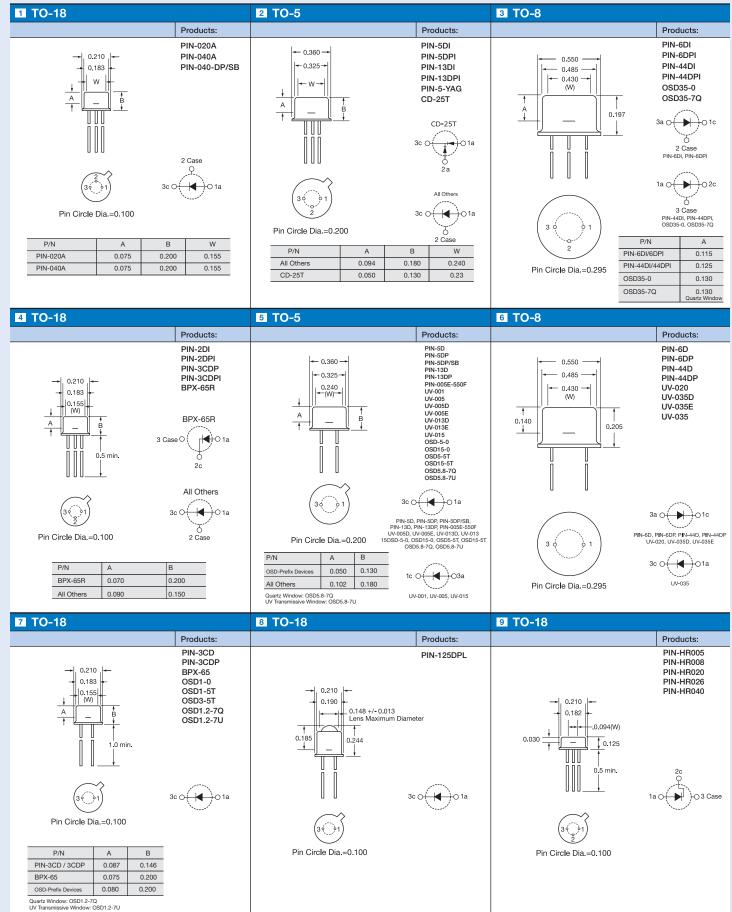
For Further Assistance Please Call One of Our Experienced Sales and Applications Engineers

310-978-0516

- Or -On the Internet at WWW.OSIOPtoelectronics.com

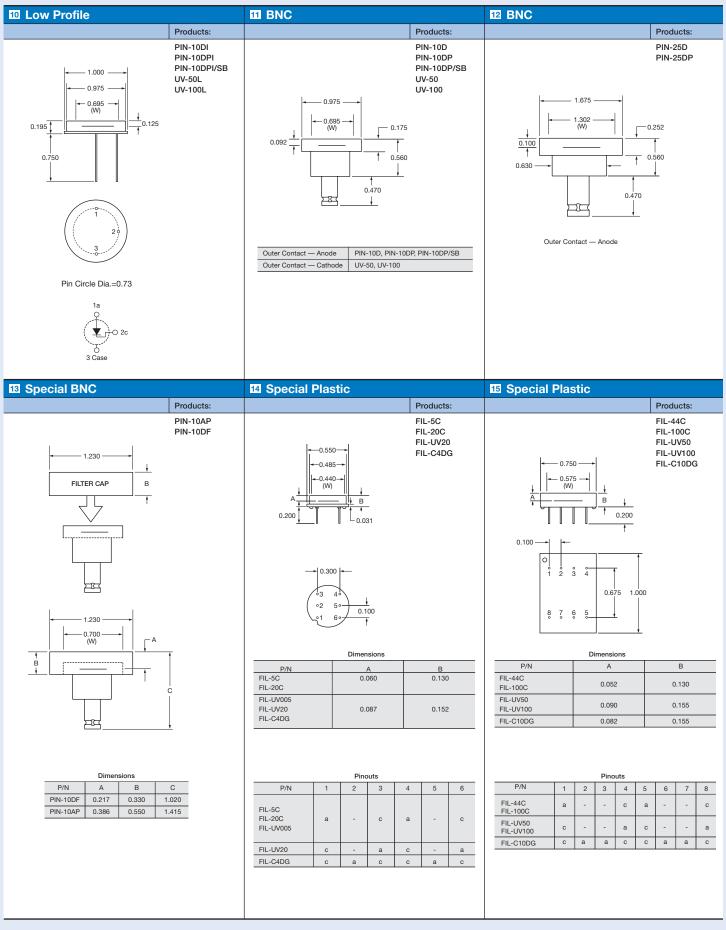
Mechanical Specifications

All units in inches. Pinouts are bottom view.



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